

IN THE DRAWINGS

The attached sheets of drawings include changes to Figures 8-10. These sheets, which include Figures 7-10, replace the original sheets including Figures 7-10.

Attachment: Replacement Sheets



This cross-sectional view shows a semiconductor device with a central gate structure. The device includes a substrate (10) with a gate stack (1, 2, 3, 4, 5, 6) and a central gate (7). The gate stack is formed on a layer (8) and is surrounded by a dielectric layer (9). The central gate (7) is positioned between two side contacts (53) and is connected to a central contact (61). The side contacts (53) are connected to the substrate (10) and are surrounded by a dielectric layer (10). The device is shown in a cross-sectional view with a central gate structure and side contacts.



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FIG. 9
BACKGROUND ART

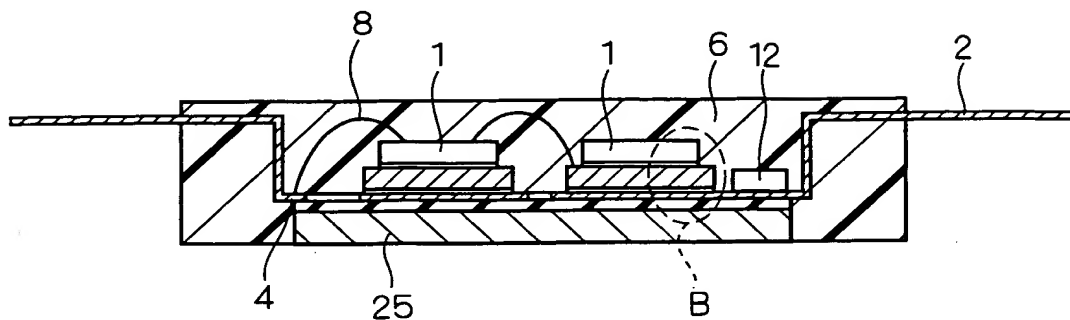


FIG. 10
BACKGROUND ART

